

Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

E·XFl

Product Status	Obsolete
Core Processor	TriCore™
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	ASC, CANbus, EBI/EMI, MLI, MSC, SSC
Peripherals	DMA, POR, WDT
Number of I/O	219
Program Memory Size	4MB (4M × 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	224K x 8
Voltage - Supply (Vcc/Vdd)	1.42V ~ 1.58V
Data Converters	A/D 48x12b
Oscillator Type	External
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	416-BBGA
Supplier Device Package	PG-BGA-416-10
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/sak-tc1797-512f180e-ac

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Introduction

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Introduction

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• (–Ore od –Abiaytpocatofactbeteen1 and 65535 – f _{GPTA} axceto – f _{GPTA} /2 axionipignalfeency Cok DitotoUnit(CDU)	
	–One bit –Piodesine cbk (bigrass $f_{\rm GPTA}$, divided $f_{\rm GPTA}$ cbksFPC1/FPC4 (pDCM	cbk, LTC ps abrcbk
Sig	nal Generation Unit	
• (• (

Interrupt Sharing Unit

• 286 interpressententing pt92 since eqs



TC1797

Electrical Parameters

Table 11 ADC Characteristics (cool) (Openting Coolitisal)							
Parameter	Symbol	V	alues	l	Jnit N	lote /	
		Min.	Тур.	Max.		Test Condition	
Gained ⁹⁾⁵⁾	EA _{GAIN} CC	_	±0.5	±3.5	LSB	12-bitconeiso Naturias ⁸⁾¹⁰⁾	
Offeteo ⁹⁾⁵⁾	EA _{OFF} CC	_	±1.0	±4.0	LSB	12-bitcores Naturas ⁸⁾¹⁰⁾	
Inpleakage contratanalg	I _{OZ1} CC	-300	-	100	A (($0\% V_{ m DDM}) < V_{ m IN} < (3\% V_{ m DDM})$	
into ADC0/1 11) 12) 13)		-100	-	200	A (:	3% V _{DDM}) < V _{IN} < (97% V _{DDM})	
		-100	-	300	PA (9	$V_{\rm DDM} > V_{\rm DDM} < V_{\rm IN} < (100\% V_{\rm DDM})$	
lnpeakage centat V _{AREF0/1/2,} prote	I _{OZ2} CC	_	-	±1.5	μA	$\begin{array}{l} 0 \; \mathrm{V} < V_{\mathrm{AREF}} < \\ V_{\mathrm{DDM,}} \; \mathbf{recreation} \\ \mathbf{rring} \end{array}$	
Introduct at $V_{\text{AREF0/1/2}}^{16)}$, prote	I _{AREF} CC	-	35	75	μA ns	$0 V < V_{AREF} < V_{DDM}^{14}$	
Tel capciance fo he tage efeence inpa ¹⁵⁾¹⁶⁾	C _{AREFTOT} CC	_	20	40	Б	8)	
Sinched capciance at he jac efeence tage into ¹⁶⁾	C _{AREFSW} CC	_	15	30	Б	8)17)	
Rebance fo he efeence bage inpu ph ¹⁵⁾	R _{AREF} CC	-	500	1000	Ω	500 Ohrinnceaed foAN[1:0] ed as efeence inp ⁸⁾	
Teal capaciance fo he anag imp ¹⁵⁾	C _{AINTOT} CC	_	25	30	Б 	1)8)	



Electrical Parameters

5.2.3 Fast Analog to Digital Converter (FADC)

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Table 13	FADC Characteristics	(Opatrog Coditosa)p
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Parameter	Symbol		Values l			lote /
		Min.	Тур.	Max.	-	Test Condition
DNL eo	EF _{DNL} C	C –	- :	t LS	в	9)
INL ed	EF _{INL} C	C –		LS	в	9)
Gadienter ⁹⁾	EF _{GRAD}	- C		5 %	Wi	h tc albato gain1, 2, 4
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Offeten 9)1)	EF _{OFF} ²⁾	-	- :	≆0 ³⁾	λγή V	Vih calbato ¹⁾
	CC	- 2	- :	90 ³⁾	λγή V	Vihtcalbato
Reference endo internal $V_{\text{FAREF}}/2$	EF _{REF} CO		- 1	£0 k∧i	-	
Anaby by	V _{DDMF} SF	R 3.13	-	3.47 ⁴⁾	V	-
lages	V_{DDAF} SF	R 1.42	-	1.58 ⁵⁾	V	-
Anabygood Tage	V _{SSAF} S	-0.1 R	-	0.1	V -	_
Anabjefeence bage	V _{FAREF} S	3.13 R	-	3.47 ⁴⁾⁶⁾	V	Nimal 3.3 V
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CEIIS	IDDAF SF	२ –		12 A		7)
Inducentiat V_{FAREF}			-	120	μA s n	Indepindentó coeixo
Independence of the second se	I _{FOZ2} CO			5500 nA	0 V	$< V_{\rm IN} < V_{\rm DDMF}$
Indexade contract at $V_{\text{FAGND}}^{8)}$	I _{FOZ3}		- 1	8	μA	$0 V < V_{IN} < V_{DDMF}$